



DMT6017LFDF

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
65V	18mΩ @ V _{GS} = 10V	8.1A
	23mΩ @ V _{GS} = 4.5V	7.1A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC Converter
- Adaptor Switch
- Wireless Charging

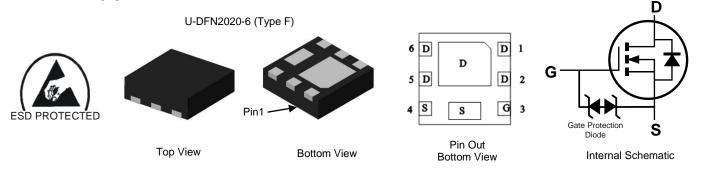
65V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.007 grams (Approximate)



Ordering Information (Note 4)

Part Number	Package	Quantity per Reel
DMT6017LFDF-7	U-DFN2020-6 (Type F)	3,000
DMT6017LFDF-13	U-DFN2020-6 (Type F)	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

 See https://www.diodes.com/quality/lead-tree/ for more information about Diodes incorporated s definitions of Halogen- and Antimony-free, "Green" and Lead-free.
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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T17 = Product Type Marking Code

YWX = Date Code Marking

Y = Year (ex: 9 = 2019)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

C = Internal Code (ex. 0 = Monda)

Date Code Key									
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	9	0	1	2	3	4	5	6	7
Week	1-26		27-52			53			
Code		A-Z		a-z			Z		
Internal Code	Sun	Мо	n	Tue	Wed	Thu		Fri	Sat
Code	Т	U		V	W	Х		Y	Z



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	65	V	
Gate-Source Voltage	V _{GSS}	±16	V	
Continuous Drain Current (Note 6) V_{GS} = 10V	Ι _D	8.1 6.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	50	A
Maximum Body Diode Continuous Current	Is	8	A	
Pulsed Body Diode Forward Current (10µs Pulse, D	I _{SM}	50	A	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	19	A	
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	18	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{ÐJA}	157	°C/W
Total Power Dissipation (Note 6)	PD	1.76	W	
Thermal Resistance, Junction to Ambient (Note 6)	R _{ÐJA}	71	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	10	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 8)										
Drain-Source Breakdown Voltage	BV _{DSS}	65			V	$V_{GS} = 0V, I_D = 10mA$				
Zero Gate Voltage Drain Current	IDSS	_		1	μA	$V_{DS} = 48V, V_{GS} = 0V$				
Gate-Source Leakage	IGSS	_	_	±10	μA	$V_{GS} = \pm 12.8 V, V_{DS} = 0 V$				
ON CHARACTERISTICS (Note 8)										
Gate Threshold Voltage	V _{GS(TH)}	1	1.4	2.3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$				
Static Drain-Source On-Resistance	Б	_	13.2	18	mΩ	$V_{GS} = 10V, I_D = 6A$				
Static Drain-Source On-Resistance	R _{DS(ON)}	_	17	23	11122	$V_{GS} = 4.5V, I_D = 4A$				
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$				
DYNAMIC CHARACTERISTICS (Note 9)	•		•	•						
Input Capacitance	Ciss	_	891							
Output Capacitance	Coss	_	223	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz				
Reverse Transfer Capacitance	Crss	_	29	_						
Gate Resistance	Rg	_	1.57		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$				
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	7.5	_						
Total Gate Charge (V _{GS} = 10V)	Qg	_	15.3		nC					
Gate-Source Charge	Q _{gs}	_	1.8		nc	$V_{DS} = 30V, I_D = 6A$				
Gate-Drain Charge	Q _{gd}	_	3.1							
Turn-On Delay Time	t _{D(ON)}	_	4.0							
Turn-On Rise Time	t _R		5.9			$V_{GS} = 10V, V_{DS} = 30V,$				
Turn-Off Delay Time	t _{D(OFF)}		11.7		ns	$R_g = 3.3\Omega, I_D = 6A$				
Turn-Off Fall Time	t _F	_	3.3							
Body Diode Reverse Recovery Time	t _{RR}	_	21.1		ns					
Body Diode Reverse Recovery Charge	Q _{RR}	_	11.9	_	nC	I _F = 6A, di/dt = 100A/μs				

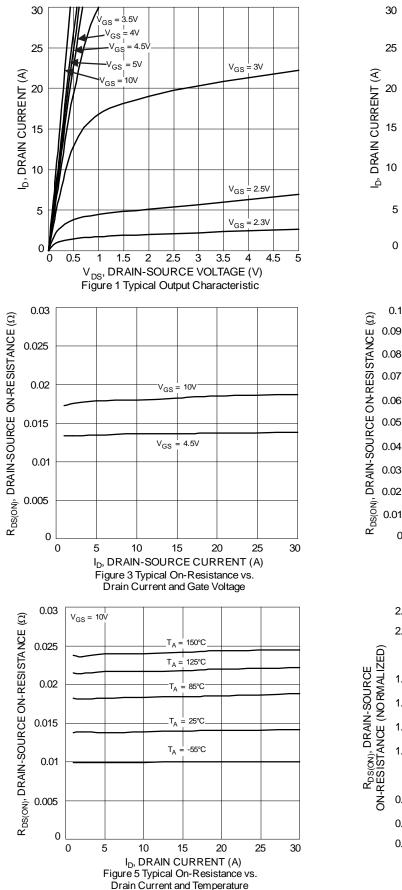
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout. Notes:

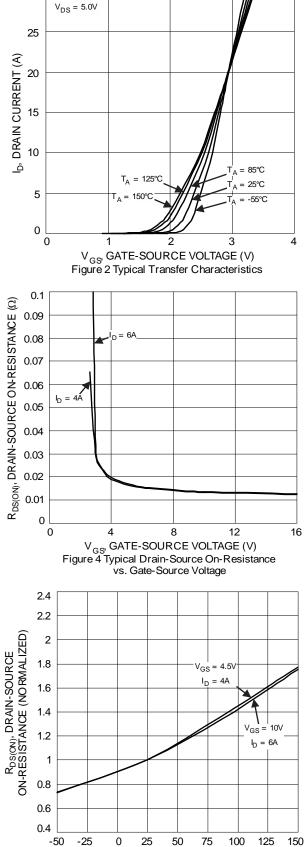
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

7. J_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.





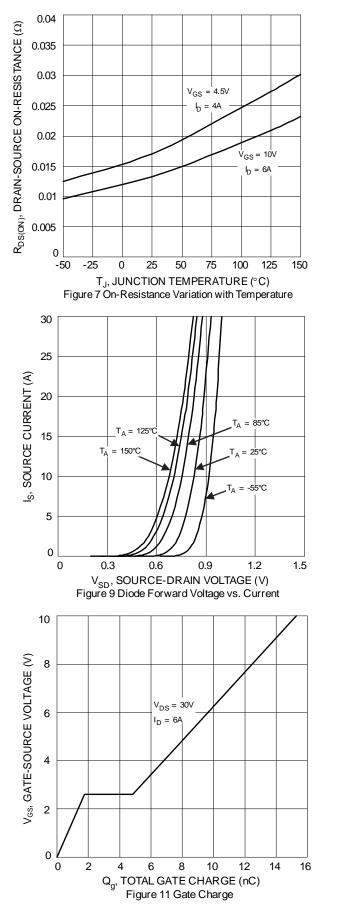




T_J, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature







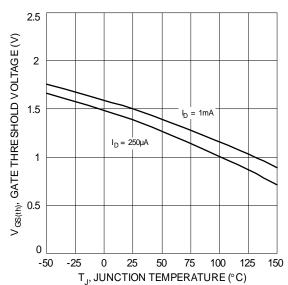
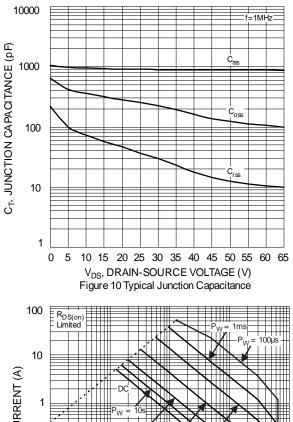
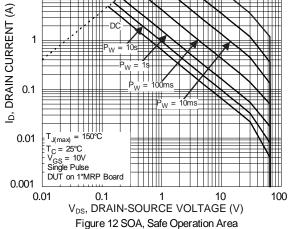
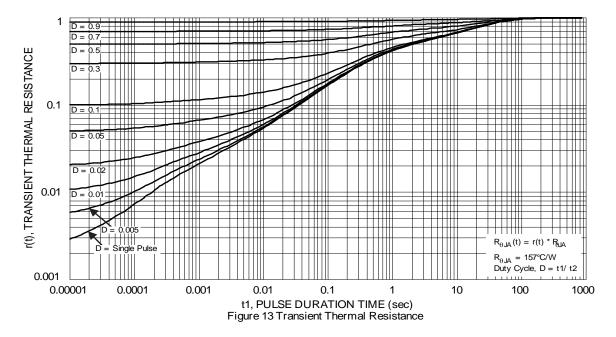


Figure 8 Gate Threshold Variation vs. Junction Temperature







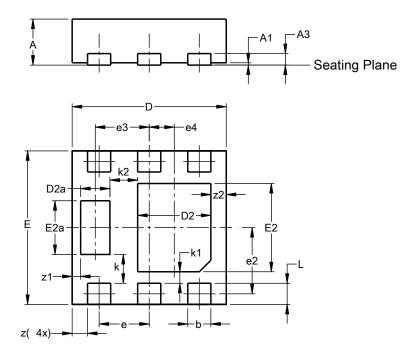




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

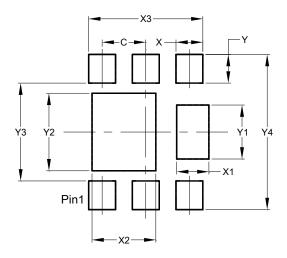


U-DFN2020-6							
(Type F) Dim Min Max Typ							
			Тур				
A	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
e	0.65 BSC						
e2	0.863 BSC						
e3		0.70 BS	С				
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
z	0.20 BSC						
z1	0.110 BSC						
z2	0.20 BSC						
All D	imens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dimensions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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